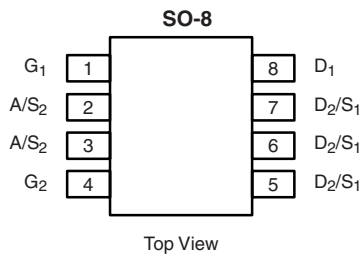


Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY				
	V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)	Q _g (Typ)
Channel-1	30	0.0185 at V _{GS} = 10 V	6.8	7.8
		0.0225 at V _{GS} = 4.5 V	6.0	
Channel-2		0.0115 at V _{GS} = 10 V	11.4	11.6
		0.016 at V _{GS} = 4.5 V	9.5	

SCHOTTKY PRODUCT SUMMARY		
V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A)
30	0.50 V at 1.0 A	2.0



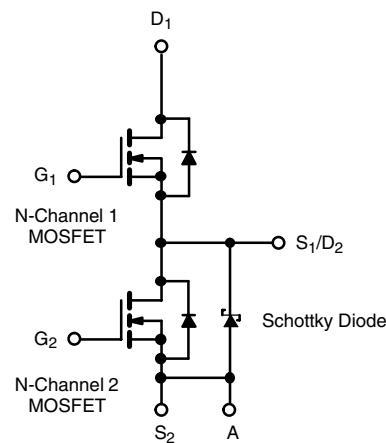
Ordering Information: Si4816BDY-T1-E3 (Lead (Pb)-free)

FEATURES

- LITTLE FOOT[®] Plus Power MOSFET
- 100 % R_g Tested



RoHS
COMPLIANT



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter	Symbol	Channel-1		Channel-2		Unit	
		10 sec	Steady State	10 sec	Steady State		
Drain-Source Voltage	V _{DS}	30				V	
Gate-Source Voltage	V _{GS}	20					
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	6.8	5.8	11.4	8.2	A
		T _A = 70 °C	5.5	4.6	9.0	6.5	
Pulsed Drain Current	I _{DM}	30		40			
Continuous Source Current (Diode Conduction) ^a	I _S	1	0.9	2.2	1.15		
Single Pulse Avalanche Current	I _{AS}	L = 0.1 mH	10		20		
Avalanche Energy			E _{AS}	5		20	
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	1.4	1.0	2.4	1.25	W
		T _A = 70 °C	0.9	0.64	1.5	0.8	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150				°C	

THERMAL RESISTANCE RATINGS									
Parameter	Symbol	Channel-1		Channel-2		Schottky		Unit	
		Typ	Max	Typ	Max	Typ	Max		
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 sec	72	90	43	53	48	60	°C/W
		Steady State	100	125	82	100	80	100	
Maximum Junction-to-Foot (Drain)	R _{thJF}	Steady State	51	63	25	30	28	35	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min	Typ ^a	Max	Unit	
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	Ch-1	1.0		3.0	V	
			Ch-2	1.0		3.0		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$	Ch-1			100	nA	
			Ch-2			100		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	Ch-1			1	μA	
			Ch-2			100		
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	Ch-1			15		
			Ch-2			2000		
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-1	20			A	
			Ch-2	30				
Drain-Source On-State Resistance ^b	$r_{DS(on)}$		Ch-1		0.0155	0.0185	Ω	
			Ch-2		0.0093	0.0115		
			Ch-1		0.0185	0.0225		
			Ch-2		0.013	0.016		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 6.8\text{ A}$	Ch-1		30		S	
			Ch-2		31			
Diode Forward Voltage ^b	V_{SD}	$I_S = 1\text{ A}, V_{GS} = 0\text{ V}$	Ch-1		0.73	1.1	V	
			Ch-2		0.47	0.5		
Dynamic^a								
Total Gate Charge	Q_g	Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = 6.8\text{ A}$	Ch-1		7.8	10	nC	
			Ch-2		11.6	18		
Gate-Source Charge	Q_{gs}	Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = -11.4\text{ A}$	Ch-1		2.9			
			Ch-2		4.8			
Gate-Drain Charge	Q_{gd}		Ch-1		2.3			
			Ch-2		3.7			
Gate Resistance	R_g		Ch-1	1.5	3.0	4.5	Ω	
			Ch-2	0.9	1.8	2.7		
Turn-On Delay Time	$t_{d(on)}$	Channel-1 $V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$	Ch-1		11	17	ns	
Rise Time	t_r		Ch-1		9	15		
			Ch-2		9	15		
Turn-Off Delay Time	$t_{d(off)}$		Channel-2 $V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$	Ch-1		24		40
				Ch-2		31		50
Fall Time	t_f			Ch-1		9		15
				Ch-2		11		17
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = 1.3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	Ch-1		20		35
		Ch-2			25	40		

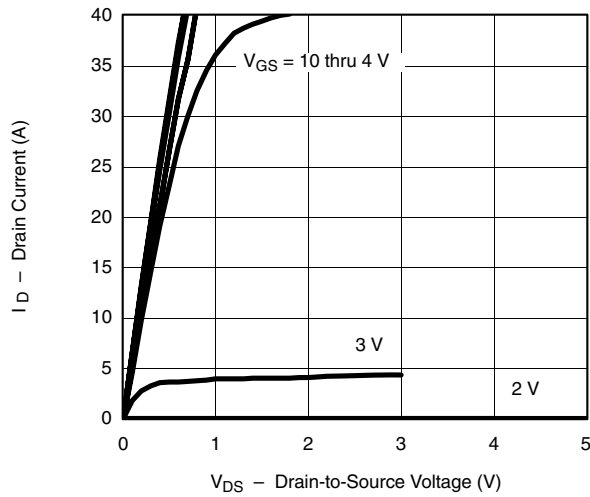
Notes:

- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

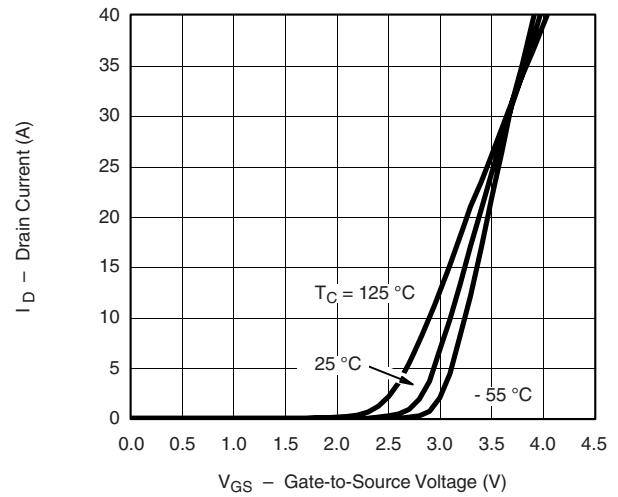
SCHOTTKY SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage Drop	V_F	$I_F = 1.0\text{ A}$		0.47	0.50	V
		$I_F = 1.0\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.36	0.42	
Maximum Reverse Leakage Current	I_{rm}	$V_r = 30\text{ V}$		0.004	0.100	mA
		$V_r = 30\text{ V}, T_J = 100\text{ }^\circ\text{C}$		0.7	10	
		$V_r = -30\text{ V}, T_J = 125\text{ }^\circ\text{C}$		3.0	20	
Junction Capacitance	C_T	$V_r = 10\text{ V}$		50		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

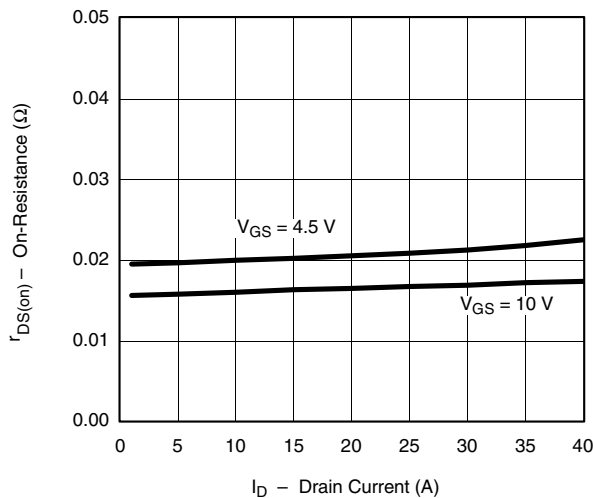
CHANNEL-1 TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless noted



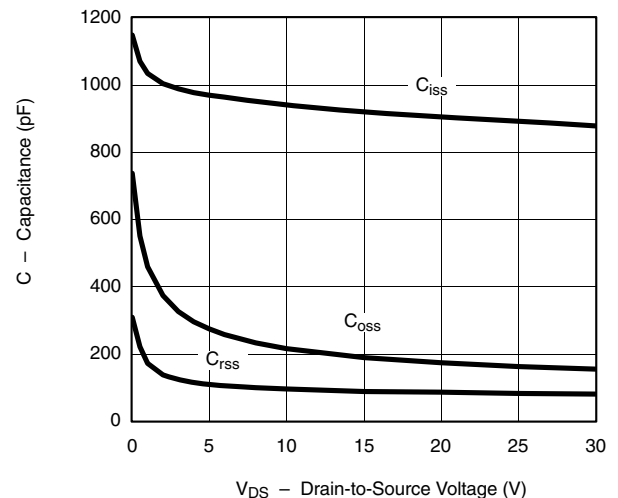
Output Characteristics



Transfer Characteristics

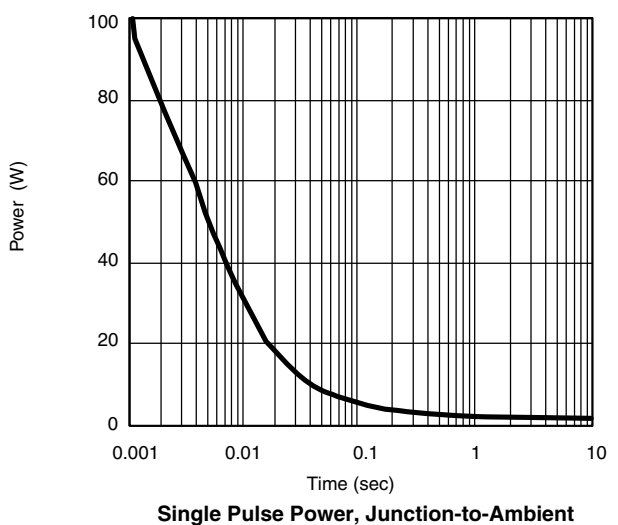
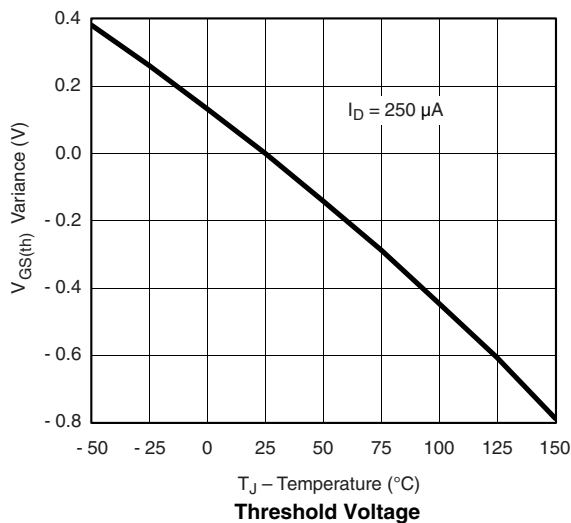
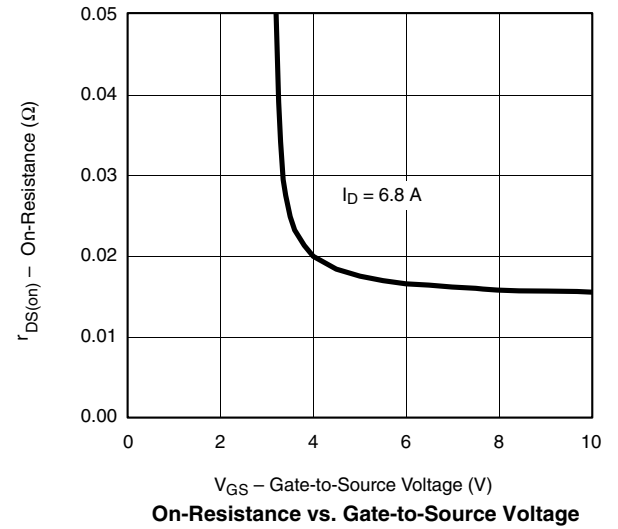
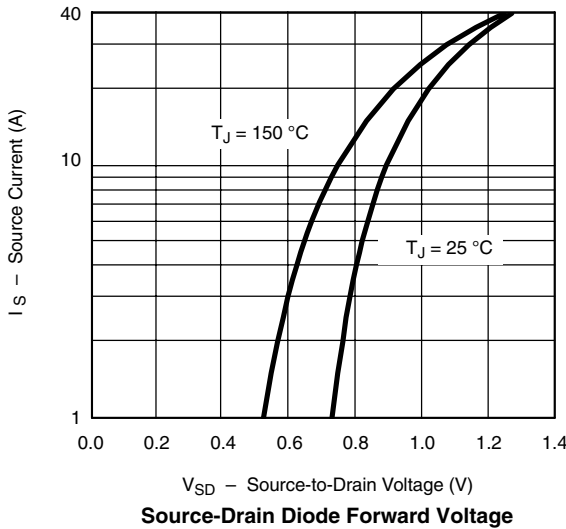
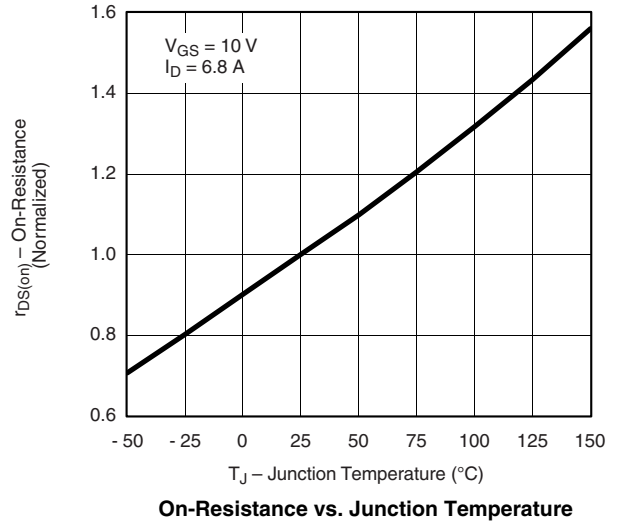
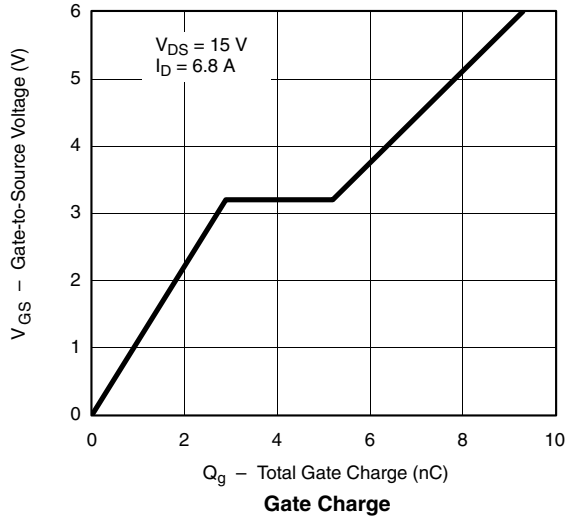


On-Resistance vs. Drain Current

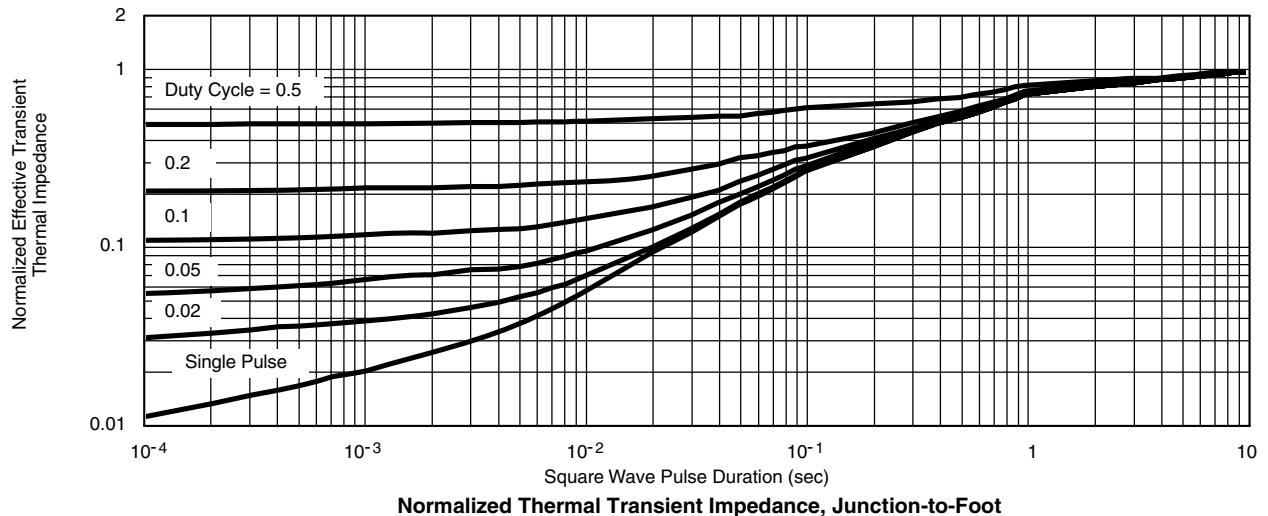
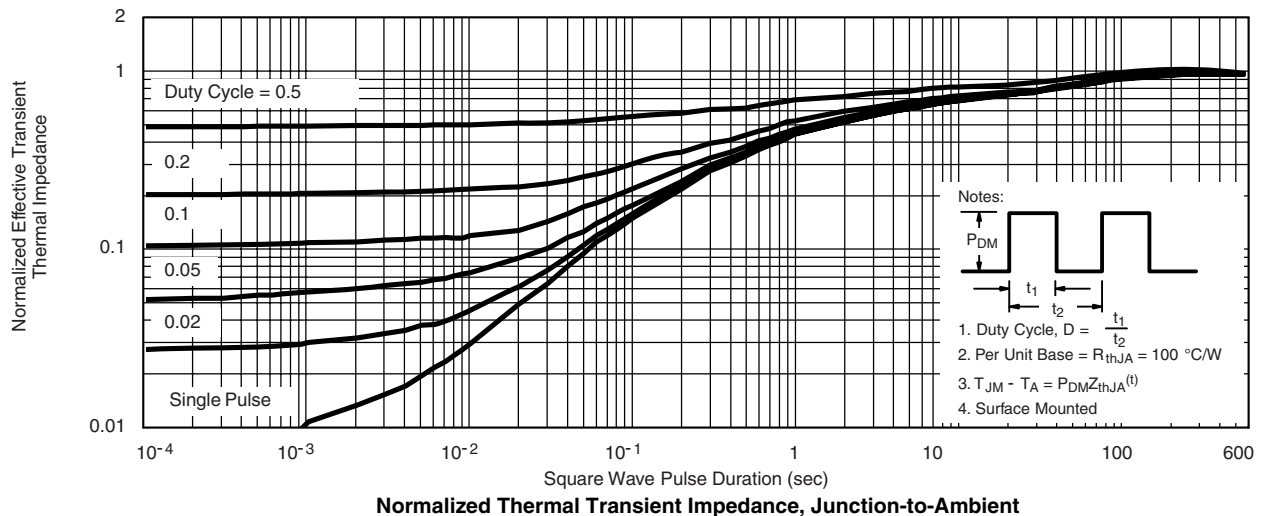
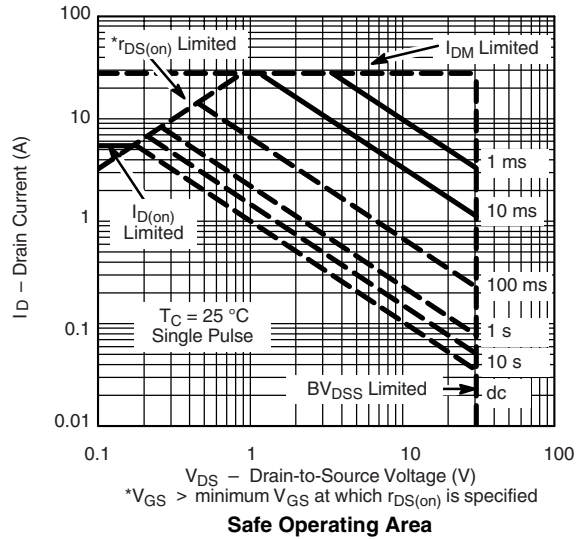


Capacitance

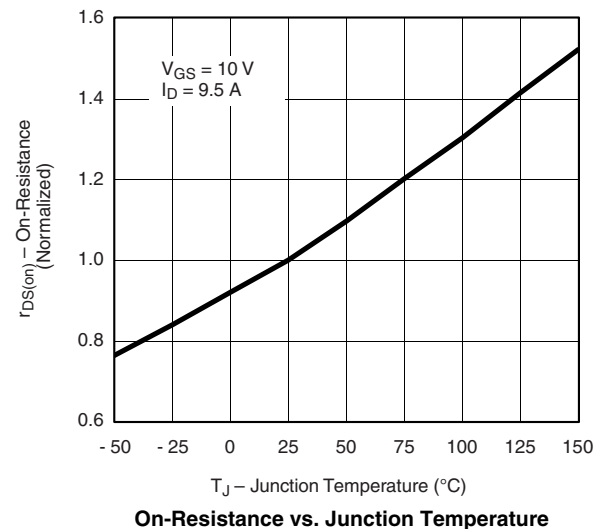
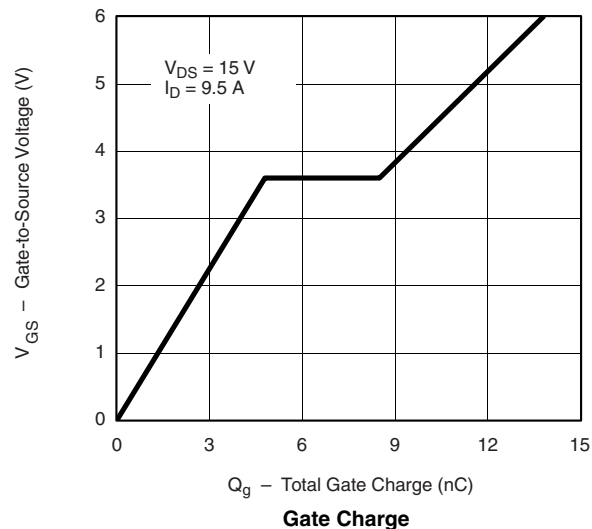
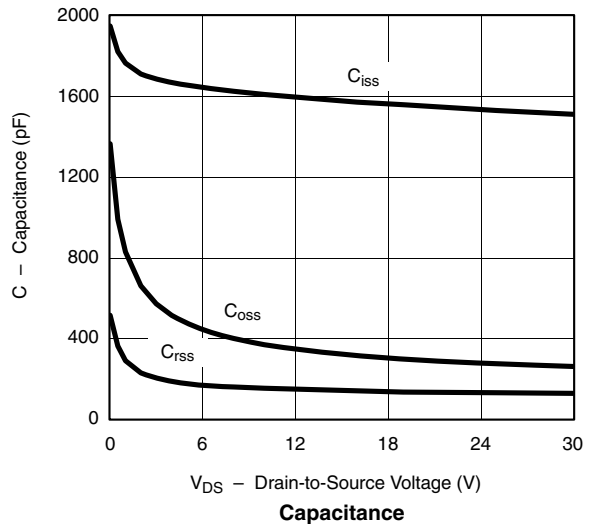
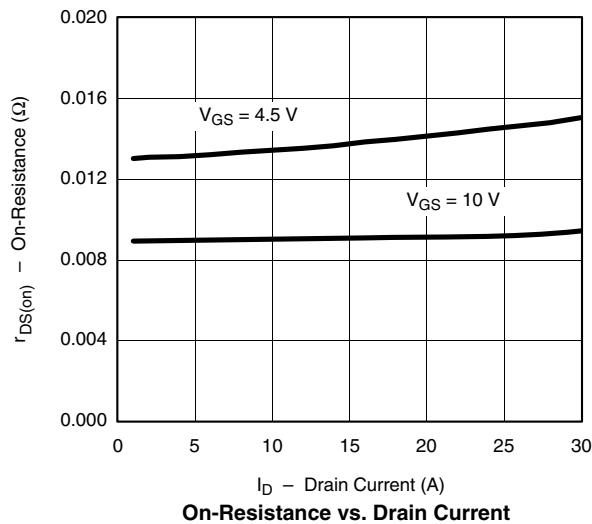
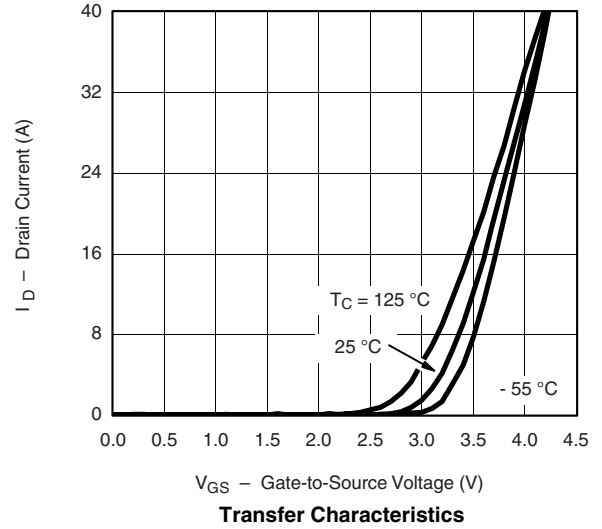
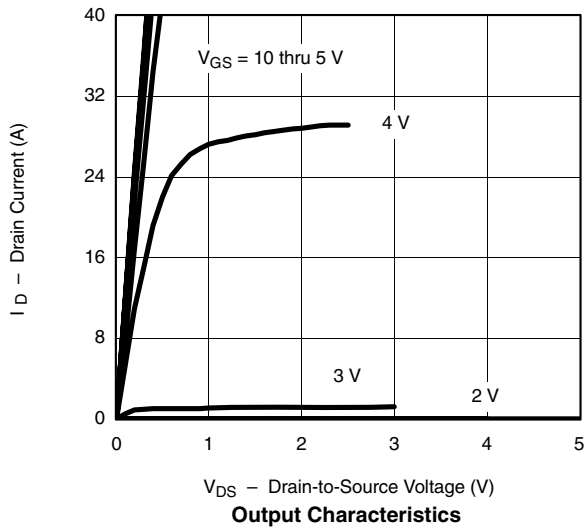
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless noted



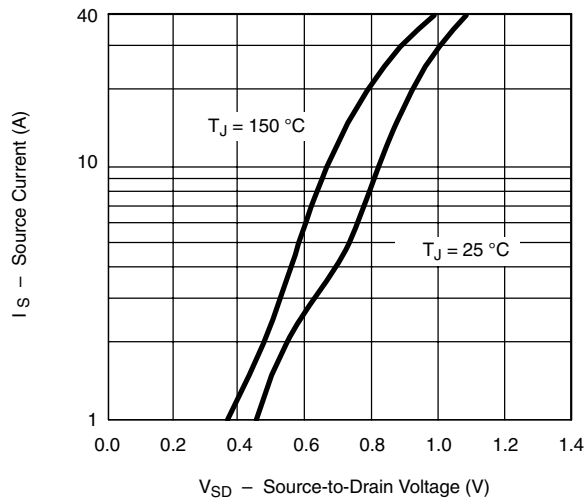
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless noted



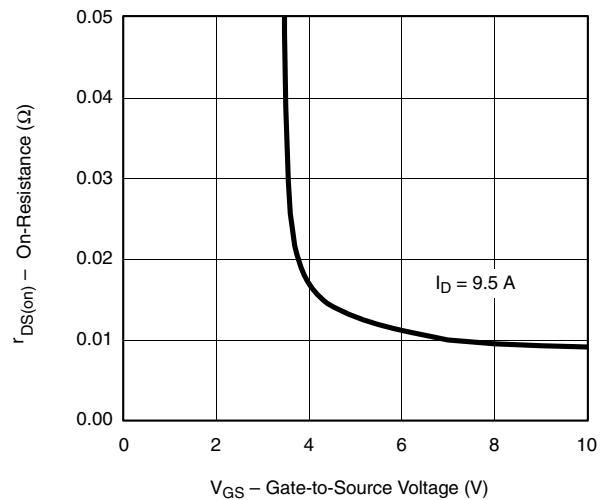
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless noted



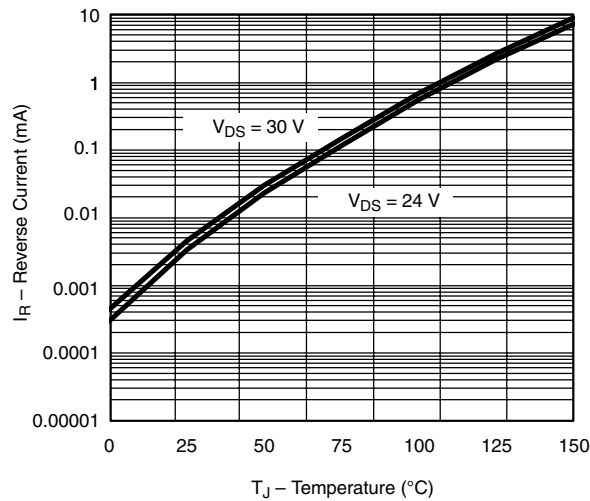
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless noted



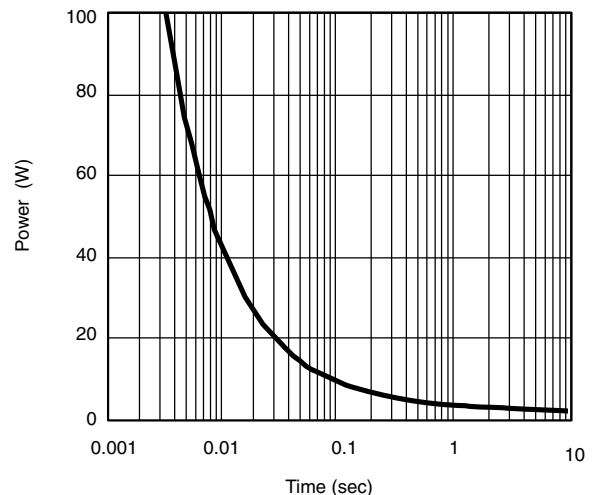
Source-Drain Diode Forward Voltage



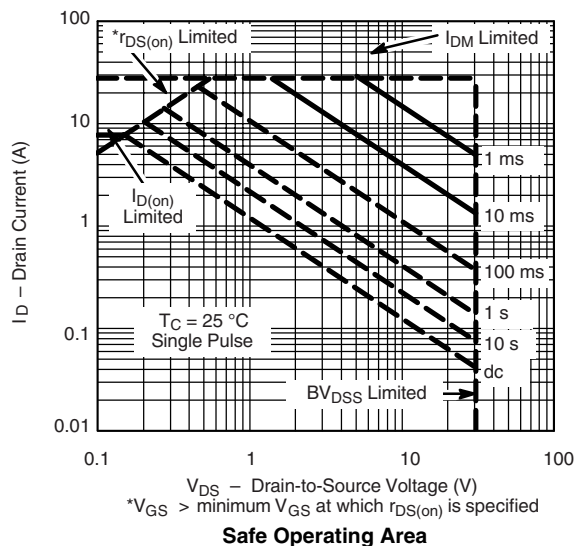
On-Resistance vs. Gate-to-Source Voltage



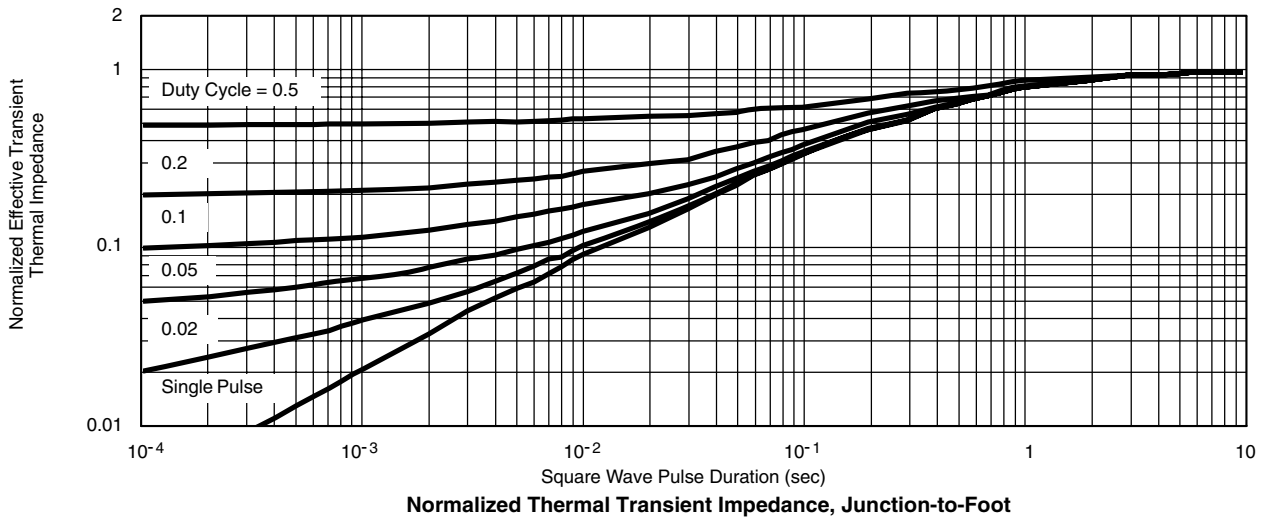
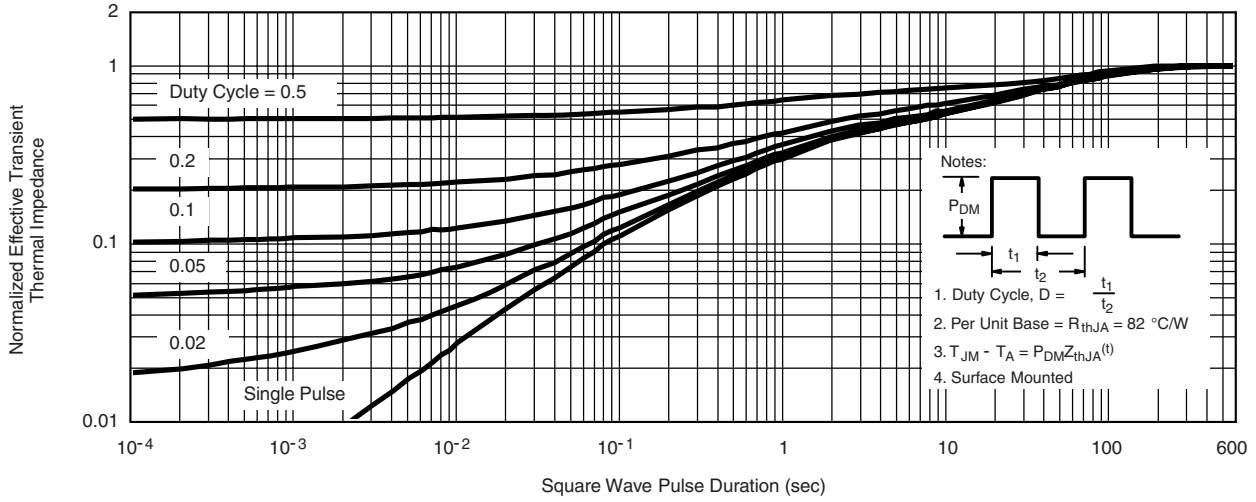
Reverse Current vs. Junction Temperature



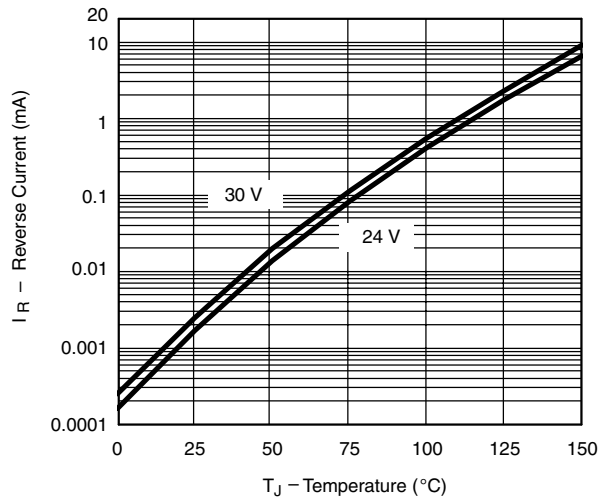
Single Pulse Power, Junction-to-Ambient



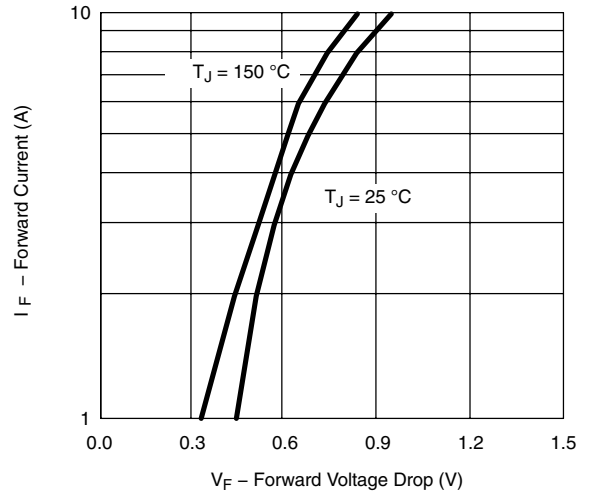
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless noted



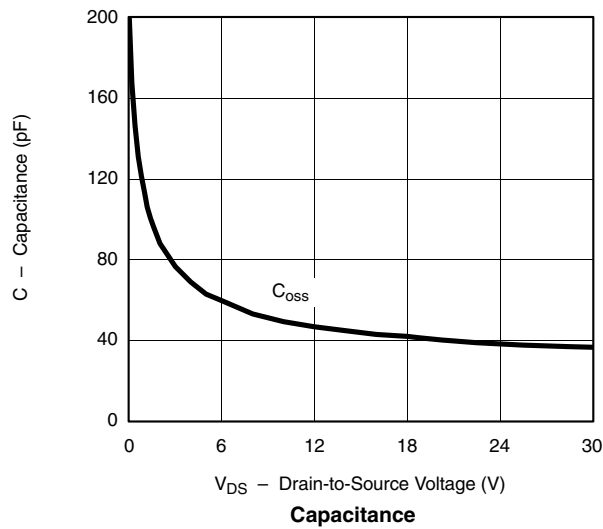
SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless noted



Reverse Current vs. Junction Temperature



Forward Voltage Drop



Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?73026>.



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